

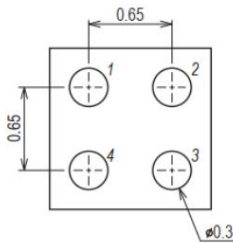
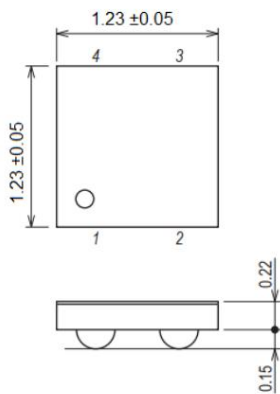
NCE Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor

Description

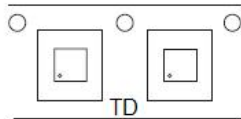
The NCE4612SP uses advanced trench technology to provide excellent $R_{SS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V while retaining a 12V $V_{GS(MAX)}$ rating. It is ESD protected. This device is suitable for use as a unidirectional or bi-directional load switch, facilitated by its common-drain configuration.

Package Dimensions

Unit : mm



Taping Type : TD



General Features

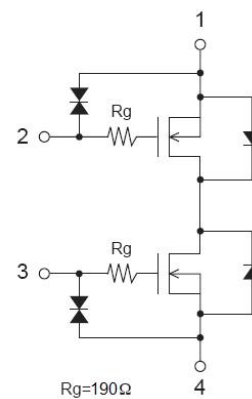
- $V_{SSS} = 24V, I_s = 6A$
- 2.5V drive
- Common-drain type
- 2KV HBM

Package Information

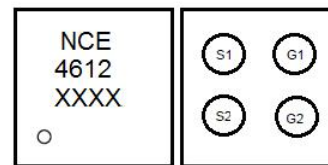
- Minimum Packing Quantity : 3,000 pcs./reel

Application

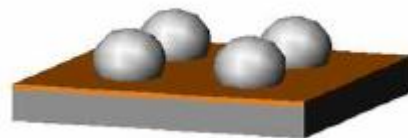
- Lithium-ion battery charging and discharging switch



Equivalent Circuit



Marking and pin assignment



CSP top view

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

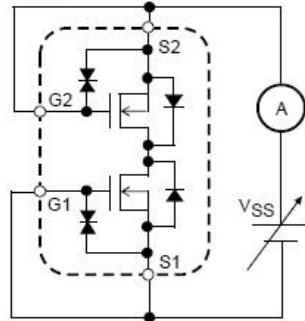
Symbol	Parameter	Limit	Unit
V_{SSS}	Source to Source Voltage	24	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_s	Source Current(DC)	6	A
I_{SP}	Source Current (Pulse)	60	A
P_T	Total Dissipation	1.6	W
T_{ch}	Channel Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	-55 To 150	$^\circ C$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

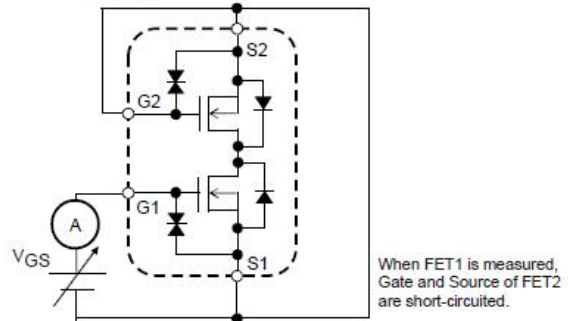
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
BV_{SSS}	Source to Source Breakdown Voltage	$I_S=1\text{mA}, V_{GS}=0\text{V}$, Test Circuit 1	24	-	-	V
I_{SSS}	Zero- Gate Voltage Source Current	$V_{SS}=20\text{V}, V_{GS}=0\text{V}$, Test Circuit 1	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{SS}=0\text{V}, V_{GS}= \pm 8\text{V}$, Test Circuit 2	-	-	± 1	μA
		$V_{SS}=0\text{V}, V_{GS}= \pm 10\text{V}$, Test Circuit 2	-	-	± 10	μA
$V_{GS(off)}$	Cutoff Voltage	$V_{SS}=10\text{V}, I_S=1\text{mA}$, Test Circuit 3	0.5	0.9	1.3	V
$ y_{gfs} $	Forward Transfer Admittance	$V_{SS}=10\text{V}, I_S=3\text{A}$, Test Circuit 4	-	3.1	-	S
$R_{SS(on)}$	Static Source to Source On-Resistance	$V_{GS}=4.5\text{V}, I_S=3\text{A}$, Test Circuit 5	26.5	27.9	34	$\text{m}\Omega$
		$V_{GS}=4.0\text{V}, I_S=3\text{A}$, Test Circuit 5	27.0	28.7	36	$\text{m}\Omega$
		$V_{GS}=3.7\text{V}, I_S=3\text{A}$, Test Circuit 5	28.0	29.4	38	$\text{m}\Omega$
		$V_{GS}=3.1\text{V}, I_S=3\text{A}$, Test Circuit 5	29.0	31.7	40	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}, I_S=3\text{A}$, Test Circuit 5	34.0	36.8	47	$\text{m}\Omega$
$t_{d(on)}$	Turn-on Delay Time	$V_{SS}=10\text{V}, I_S=3\text{A}, V_{GS}=4.5\text{V}$ Test Circuit 7	-	21	-	nS
t_r	Turn-on Rise Time		-	235	-	nS
$t_{d(off)}$	Turn-Off Delay Time		-	135	-	nS
t_f	Turn-Off Fall Time		-	210	-	nS
Q_g	Total Gate Charge	$V_{SS}=10\text{V}, I_S=6\text{A}, V_{GS}=4.5\text{V}$ Test Circuit 8	-	10	-	nC
C_{iss}	Input Capacitance	$V_{SS}=10\text{V}, V_{GS}=0\text{V},$ $F=1.0\text{MHz}$	-	873.5	-	PF
C_{oss}	Output Capacitance		-	70	-	PF
C_{rss}	Reverse Transfer Capacitance		-	50	-	PF
$V_{F(S-S)}$	Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=1\text{A}$	-	-	1.4	V

Test Circuit

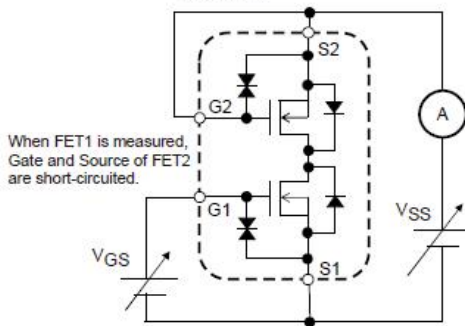
Test Circuit 1
I_{SS}



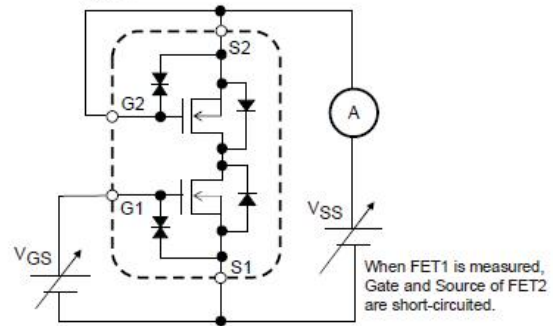
Test Circuit 2
I_{GSS}



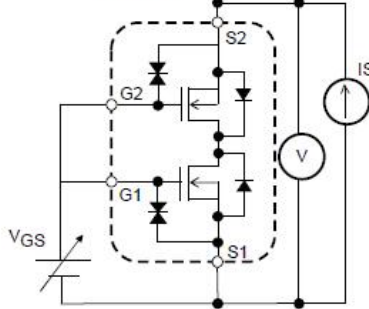
Test Circuit 3
V_{GS(off)}



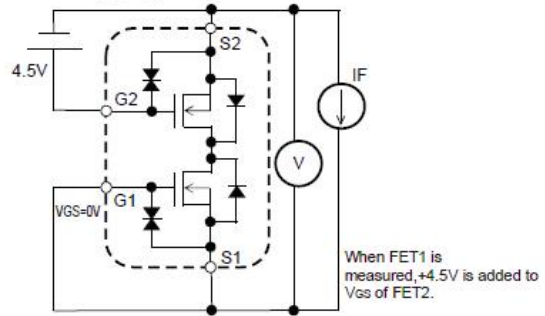
Test Circuit 4
|y_{fs}|



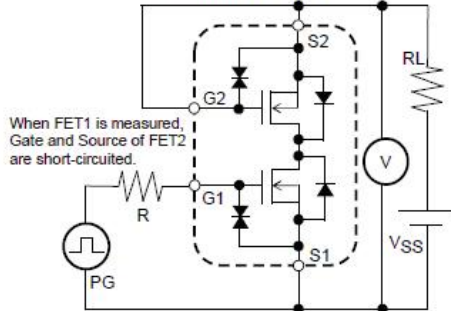
Test Circuit 5
R_{SS(on)}



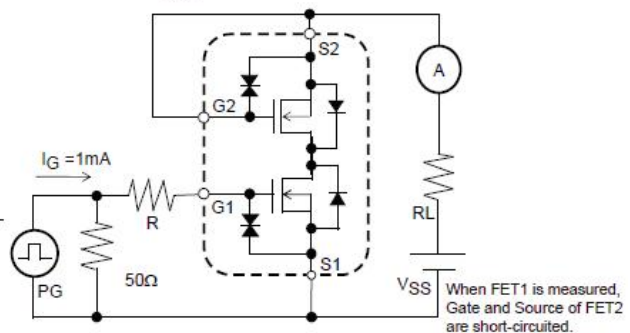
Test Circuit 6
V_{F(S-S)}



Test Circuit 7
t_{d(on)}, t_r, t_{d(off)}, t_f



Test Circuit 8
Q_g



Typical Electrical and Thermal Characteristics (Curves)

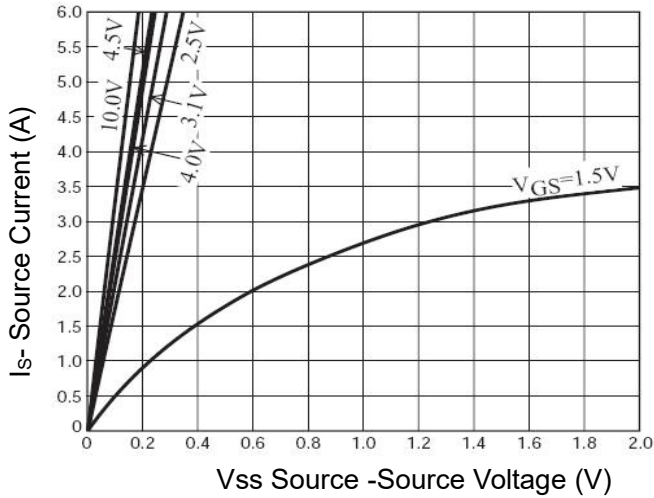


Figure 1 On-Region Characteristics

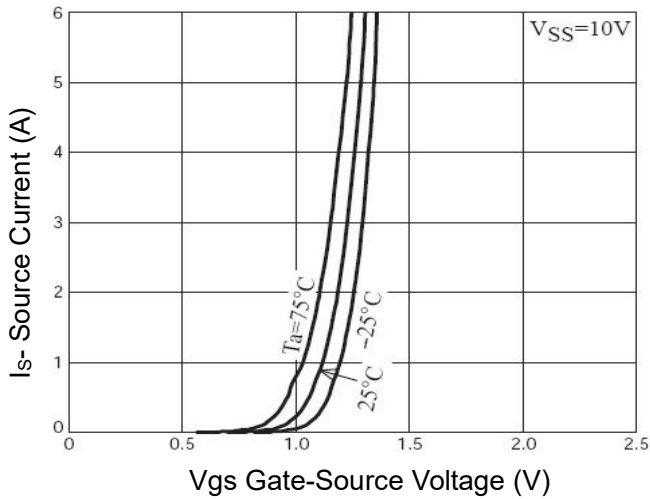


Figure 2 Transfer Characteristics

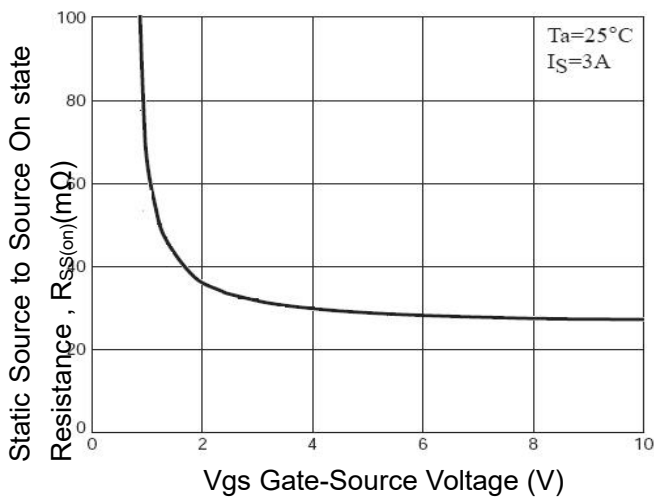


Figure 3 On-Resistance-Gate-Source Voltage

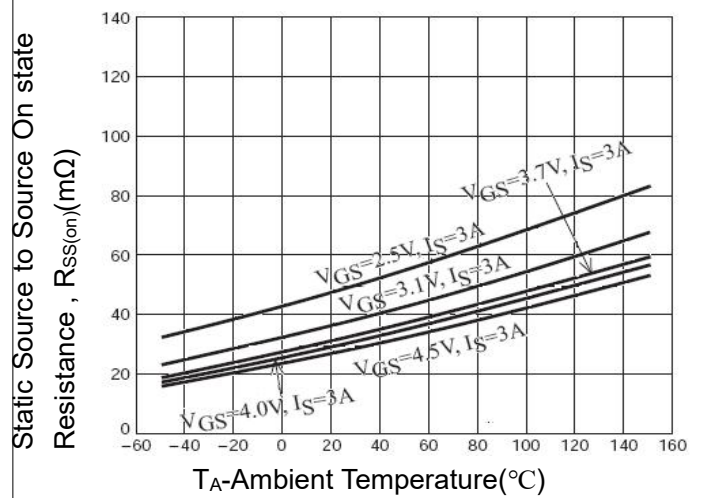


Figure 4 Rss(on)- Ambient Temperature

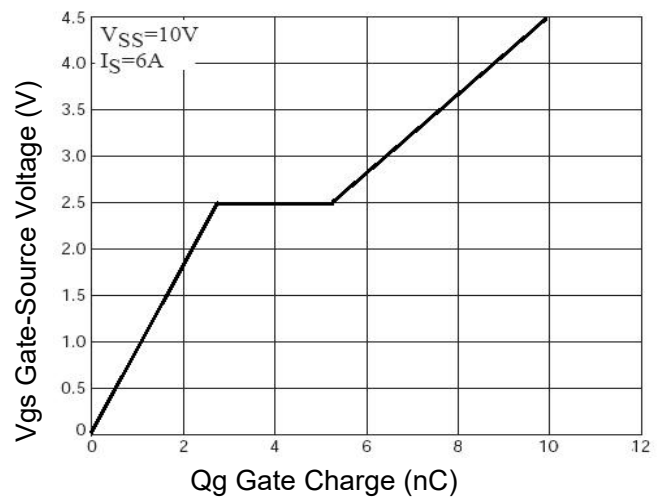


Figure 5 Gate Charge

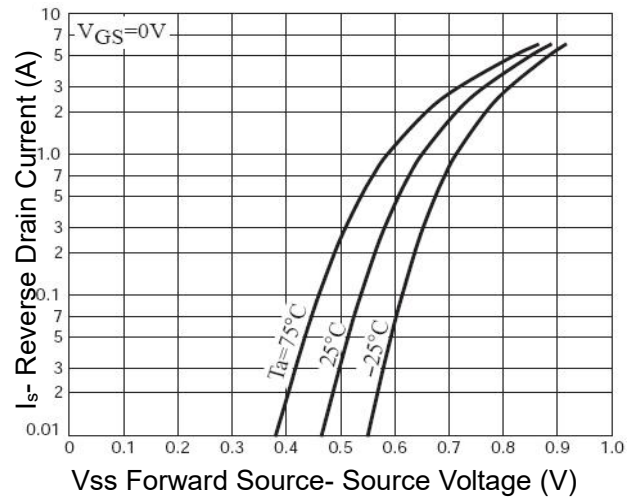


Figure 6 Body-Diode Characteristics

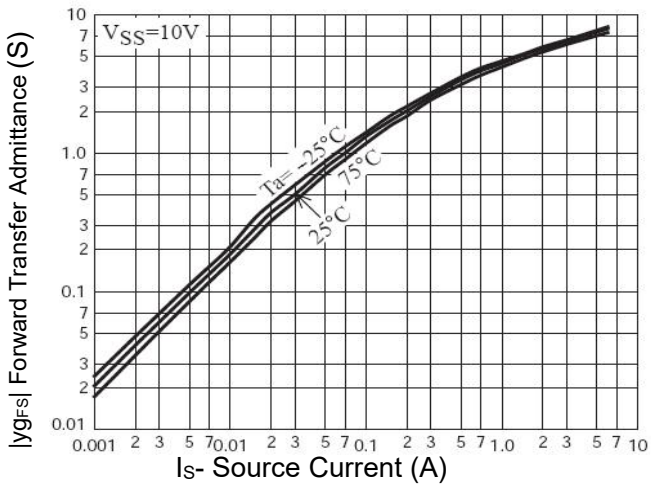


Figure 7 $|y_{fs}|$ vs I_s

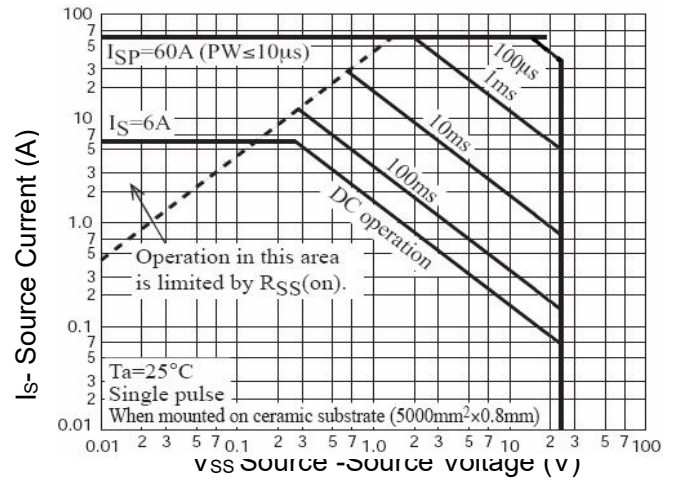


Figure 8 Safe Operation Area

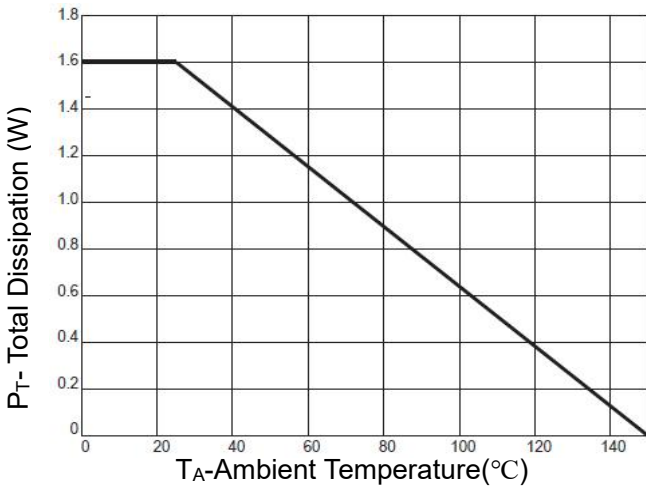


Figure 9 P_T Dissipation De-rating

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